

Data sheet acquired from Harris Semiconductor SCHS209A

CD74HC4067, CD74HCT4067

High-Speed CMOS Logic 16-Channel Analog Multiplexer/Demultiplexer

February 1998 - Revised July 2000

Features

- · Wide Analog Input Voltage Range
- Low "ON" Resistance

- V _{CC} = 4.5V	
- V 6V	600 (Typ)

- Fast Switching and Propagation Speeds
- "Break-Before-Make" Switching. 6ns (Typ) at 4.5V
- Available in Both Narrow and Wide-Body Plastic Packages
- Fanout (Over Temperature Range)
 - Standard Outputs................ 10 LSTTL Loads
 - Bus Driver Outputs 15 LSTTL Loads
- Wide Operating Temperature Range . . . -55°C to 125°C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- HC Types
 - 2V to 6V Operation
 - High Noise Immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC} at V_{CC} = 5V
- HCT Types
 - 4.5V to 5.5V Operation
 - Direct LSTTL Input Logic Compatibility,
 V_{IL}= 0.8V (Max), V_{IH} = 2V (Min)
 - CMOS Input Compatibility, $I_I \le 1\mu A$ at V_{OL} , V_{OH}

Description

The CD74HC4067 and CD74HCT4067 devices are digitally controlled analog switches that utilize silicon-gate CMOS technology to achieve operating speeds similar to LSTTL, with the low power consumption of standard CMOS integrated circuits.

These analog multiplexers/demultiplexers control analog voltages that may vary across the voltage supply range. They are bidirectional switches thus allowing any analog input to be used as an output and vice-versa. The switches have low "on" resistance and low "off" leakages. In addition, these devices have an enable control which when high will disable all switches to their "off" state.

Ordering Information

PART NUMBER	TEMP. RANGE (°C)	PACKAGE
CD74HC4067E	-55 to 125	24 Ld PDIP
CD74HC4067M	-55 to 125	24 Ld SOIC
CD74HC4067SM	-55 to 125	24 Ld SSOP
CD74HCT4067M	-55 to 125	24 Ld SOIC

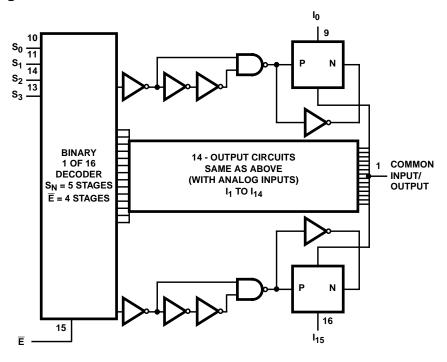
NOTES:

- 1. When ordering, use the entire part number. Add the suffix 96 to obtain the variant in the tape and reel.
- Wafer and die is available that meets all electrical specifications. Please contact your local TI sales office or customer service for ordering information.

Pinout

CD74HC4067, CD74HCT4067 (PDIP, SOIC, SSOP) TOP VIEW

Functional Diagram



TRUTH TABLE

S0	S 1	S2	S 3	Ē	SELECTED CHANNEL
Х	Х	Х	Х	1	None
0	0	0	0	0	0
1	0	0	0	0	1
0	1	0	0	0	2
1	1	0	0	0	3
0	0	1	0	0	4
1	0	1	0	0 0	
0	1	1	0	0	6
1	1	1	0	0	7
0	0	0	1	0	8
1	0	0	1	0	9
0	1	0	1	0	10
1	1	0	1	0	11
0	0	1	1	0	12
1	0	1	1	0	13
0	1	1	1	0	14
1	1	1	1	0	15

NOTE:

H = High Level

L = Low Level

X = Don't Care

Absolute Maximum Ratings

DC Supply Voltage, V _{CC}
(Voltages Referenced to Ground)0.5V to 7V
DC Input Diode Current, I _{IK}
For $V_I < -0.5V$ or $V_I > V_{CC} + 0.5V$
DC Drain Current, I _O
For $-0.5V < V_O < V_{CC} + 0.5V$
DC Output Diode Current, I _{OK}
For $V_O < -0.5V$ or $V_O > V_{CC} + 0.5V$
DC Output Source or Sink Current per Output Pin, IO
For $V_O > -0.5V$ or $V_O < V_{CC} + 0.5V$
DC V _{CC} or Ground Current, I _{CC}

Thermal Information

Thermal Resistance (Typical, Note 3)	θ_{JA} (oC/W)
E Package	67
M Package	46
SM Package	63
Maximum Junction Temperature (Plastic Package)	150°C
Maximum Storage Temperature Range6	65°C to 150°C

Operating Conditions

Temperature Range, T _A	55°C to 125°C
HC Types	2V to 6V
HCT Types	
DC Input or Output Voltage, V _I , V _O	0V to V _{CC}
Input Rise and Fall Time	
2V	1000ns (Max)
4.5V	500ns (Max)
6V	400ns (Max)

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE

3. θ_{JA} is calculated in accordance with JESD 51.

DC Electrical Specifications

			TEST CONDITIONS		25		25°C		O 85°C	-55°C T	O 125°C	
PARAMETER	SYMBOL	V _I (V)	V _{IS} (V)	V _{CC} (V)	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNITS
HC TYPES												
High Level Input	V _{IH}	-	-	2	1.5	-	-	1.5	-	1.5	-	V
Voltage				4.5	3.15	-	-	3.15	-	3.15	-	٧
				6	4.2	-	-	4.2	-	4.2	-	٧
Low Level Input	V _{IL}	-	-	2	-	-	0.5	-	0.5	-	0.5	٧
Voltage				4.5	-	-	1.35	-	1.35	-	1.35	٧
				6	-	-	1.8	-	1.8	-	1.8	V
Maximum "ON"	R _{ON}	V _{CC} or	r V _{CC} or GND	4.5	-	70	160	-	200	-	240	Ω
Resistance I _O = 1mA		GND		6	-	60	140	-	175	-	210	Ω
		V _{CC} to	V _{CC} to	4.5	-	90	180	-	225	-	270	Ω
		GND	GND	6	-	80	160	-	200	-	240	Ω
Maximum "ON"	ΔR _{ON}	-	-	4.5	-	10	-	-	-	-	-	Ω
Resistance Between Any Two Switches				6	-	8.5	-	-	-	-	-	Ω
Switch "Off" Leakage Current 16 Channels	I _{IZ}	E = V _{CC}	V _{CC} or GND	6	-	-	±0.8	-	±8	-	±8	μА
Logic Input Leakage Current	I _I	V _{CC} or GND	-	6	-	-	±0.1	-	±1	-	±1	μА
Quiescent Device Current I _O = 0mA	Icc	V _{CC} or GND	-	6	-	-	8	-	80	-	160	μА

DC Electrical Specifications (Continued)

		TE CONDI	ST ITIONS		25°C		-40°C TO 85°C		-55°C T	O 125°C		
PARAMETER	SYMBOL	V _I (V)	V _{IS} (V)	V _{CC} (V)	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNITS
HCT TYPES	ICT TYPES											
High Level Input Voltage	V _{IH}	-	-	4.5	2	-	-	2	-	2	-	V
Low Level Input Voltage	V _{IL}	-	-	4.5	-	-	0.8	-	0.8	-	0.8	V
Maximum "ON" Resistance	R _{ON}	V _{CC} or GND	V _{CC} or GND	4.5	-	70	160	-	200	-	240	Ω
I _O = 1mA		V _{CC} to GND	V _{CC} to GND	4.5	-	90	180	-	225	-	270	Ω
Maximum "ON" Resistance Between Any Two Switches	ΔR _{ON}	-	-	4.5	-	10	-	-	-	-	-	Ω
Switch "Off" Leakage Current 16 Channels	l _{IZ}	Ē = V _{CC}	V _{CC} or GND	6	-	-	±0.8	-	±8	-	±8	μА
Logic Input Leakage Current	lı	V _{CC} or GND (Note 5)	-	6	-	-	±0.1	-	±1	-	±1	μА
Quiescent Device Current	l _{CC}	V _{CC} or GND	-	6	-	-	8	-	80	-	160	μА
Additional Quiescent Device Current Per Input Pin: 1 Unit Load	ΔI _{CC} (Note 4)	V _{CC} -2.1	-	-	ī	100	360	-	450	-	490	μА

NOTES:

- 4. For dual-supply systems theoretical worst case (V_I = 2.4V, V_{CC} = 5.5V) specification is 1.8mA.
- 5. Any voltage between $V_{\mbox{\footnotesize CC}}$ and GND.

HCT Input Loading Table

INPUT	UNIT LOAD
S ₀ - S ₃	0.5
Ē	0.3

NOTE: Unit Load is ΔI_{CC} limit specified in DC Electrical Specifications table, e.g., $360\mu A$ max at $25^{\circ}C$.

Switching Specifications Input $t_{\text{r}}, \, t_{\text{f}} = 6 \text{ns}$

		TEST	v _{cc}		25°C		-40°C T	O 85°C	-55°C T	O 125°C	
PARAMETER	SYMBOL	CONDITIONS		MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNITS
HC TYPES											
Propagation Delay Time	t _{PLH} , t _{PHL}	C _L = 50pF	2	-	-	75	-	95	-	110	ns
Switch In to Out			4.5	-	-	15	-	19	-	22	ns
			6	-	-	13	-	16	-	19	ns
		C _L = 15pF	5	-	6	-	-	-	-	-	ns
Switch Turn On	t _{PZH} , t _{PZL}	C _L = 50pF	2	-	-	275	-	345	-	415	ns
E to Out			4.5	-	-	55	-	69	-	83	ns
			6	-	-	47	-	59	-	71	ns
		C _L = 15pF	5	-	23	-	-	-	-	-	ns

Switching Specifications Input t_r , $t_f = 6ns$ (Continued)

		TEST	v _{cc}		25°C		-40°C T	O 85°C	-55°C T	O 125°C	
PARAMETER	SYMBOL	CONDITIONS	(V)	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNITS
Switch Turn On	t _{PZH} , t _{PZL}	C _L = 50pF	2	-	-	300	-	375	-	450	ns
Sn to Out			4.5	-	-	60	-	75	-	90	ns
			6	-	-	51	-	64	-	76	ns
		C _L = 15pF	5	-	25	-	-	-	-	-	ns
Switch Turn Off	t _{PHZ} , t _{PLZ}	C _L = 50pF	2	-	-	275	-	345	-	415	ns
E to Out			4.5	-	-	55	-	69	-	83	ns
			6	-	-	47	-	59	-	71	ns
		C _L = 15pF	5	-	23	-	-	-	-	-	ns
Switch Turn Off	t _{PHZ} , t _{PLZ}	C _L = 50pF	2	-	-	290	-	365	-	435	ns
Sn to Out			4.5	-	-	58	-	73	-	87	ns
			6	-	-	49	-	62	-	74	ns
		C _L = 50pF	5	-	21	-	-	-	-	-	ns
Input (Control) Capacitance	C _I	-	-	-	-	10	-	10	-	10	pF
Power Dissipation Capacitance (Notes 6, 7)	C _{PD}	-	5	-	93	-	-	-	-	-	pF
HCT TYPES											
Propagation Delay Time	t _{PLH} , t _{PHL}	C _L = 50pF	4.5	-	-	15	-	19	-	22	ns
Switch In to Out		C _L = 15pF	5	-	6	-	-	-	-	-	ns
Switch Turn On	t _{PZH} , t _{PZL}	C _L = 50pF	4.5	-	-	60	-	75	-	90	ns
E to Out		C _L = 15pF	5	-	25	-	-	-	-	-	ns
Switch Turn On	t _{PZH} , t _{PZL}	C _L = 50pF	4.5	-	-	60	-	75	-	90	ns
Sn to Out		C _L = 15pF	5	-	25	-	-	-	-	-	ns
Switch Turn Off	t _{PHZ} , t _{PLZ}	C _L = 50pF	4.5	-	-	55	-	69	-	83	ns
E to Out		C _L = 15pF	5	-	23	-	-	-	-	-	ns
Switch Turn Off	t _{PHZ} , t _{PLZ}	C _L = 50pF	4.5	-	-	58	-	73	-	87	ns
Sn to Out		C _L = 15pF	5	-	21	-	-	-	-	-	ns
Input (Control) Capacitance	CI	-	-	-	-	10	-	10	-	10	pF
Power Dissipation Capacitance (Notes 6, 7)	C _{PD}	-	5	-	96	-	-	-	-	-	pF

NOTES:

^{6.} $C_{\mbox{\scriptsize PD}}$ is used to determine the dynamic power consumption, per package.

^{7.} $P_D = C_{PD} \, V_{CC}^2 \, f_i + \Sigma \, (C_L + C_S) \, V_{CC}^2 \, f_o$ where f_i = input frequency, f_o = output frequency, C_L = output load capacitance, C_S = switch capacitance, V_{CC} = supply voltage.

Analog Channel Specifications T_A = 25°C

PARAMETER	TEST CONDITIONS	V _{CC} (V)	нс/нст	UNITS
Switch Frequency Response Bandwidth at -3dB (Figure 2)	Figure 4, Notes 8, 9	4.5	89	MHz
Sine Wave Distortion	Figure 5	4.5	0.051	%
Feedthrough Noise E to Switch	Figure 6, Notes 9, 10	4.5	TBE	mV
Feedthrough Noise S to Switch			TBE	mV
Switch "OFF" Signal Feedthrough (Figure 3)	Figure 7	4.5	-75	dB
Switch Input Capacitance, C _S		-	5	pF
Common Capacitance, C _{COM}		-	50	pF

NOTES:

- 8. Adjust input level for 0dBm at output, f = 1MHz.
- 9. V_{IS} is centered at $V_{CC}/2$.
- 10. Adjust input for 0dBm at $V_{\mbox{\scriptsize IS}}$.

Typical Performance Curves

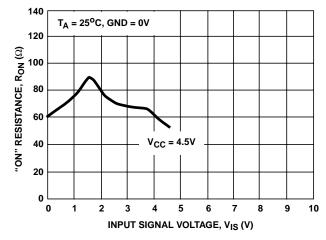


FIGURE 1. TYPICAL "ON" RESISTANCE vs INPUT SIGNAL VOLTAGE

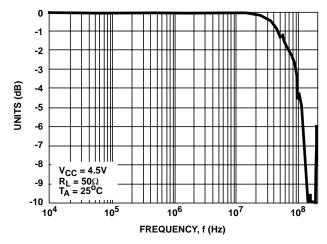


FIGURE 2. TYPICAL SWITCH FREQUENCY RESPONSE

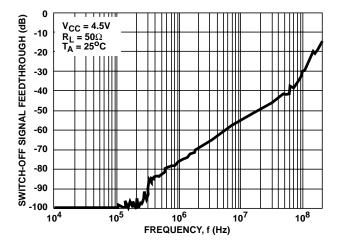


FIGURE 3. TYPICAL SWITCH-OFF SIGNAL FEEDTHROUGH vs FREQUENCY

Analog Test Circuits

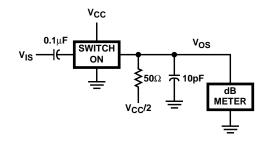


FIGURE 4. FREQUENCY RESPONSE TEST CIRCUIT

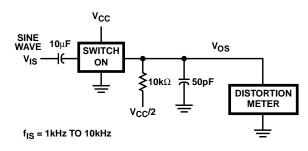


FIGURE 5. SINE WAVE DISTORTION TEST CIRCUIT

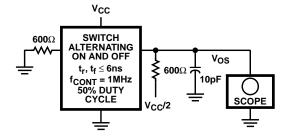


FIGURE 6. CONTROL-TO-SWITCH FEEDTHROUGH NOISE TEST CIRCUIT

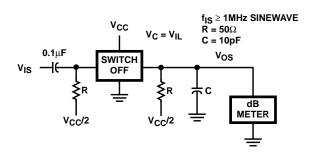


FIGURE 7. SWITCH OFF SIGNAL FEEDTHROUGH TEST CIRCUIT

Test Circuits and Waveforms

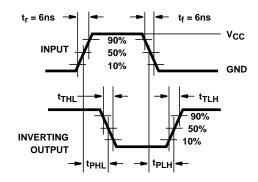


FIGURE 8. HC TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

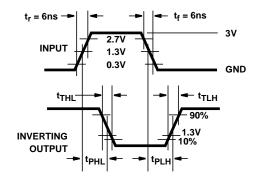


FIGURE 9. HCT TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

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